

Data Sheet June 6, 2006 FN2944.8

## 750MHz, Low Distortion Unity Gain, Closed Loop Buffer

The HFA1110 is a unity gain closed loop buffer that achieves -3dB bandwidth of 750MHz, while offering excellent video performance and low distortion. Manufactured on Intersil's proprietary complementary bipolar UHF-1 process, the HFA1110 also offers very fast slew rate, and high output current. It is one more example of Intersil's intent to enhance its leadership position in products for high speed signal processing applications.

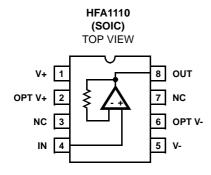
The HFA1110's settling time of 11ns to 0.1%, low distortion and ability to drive capacitive loads make it an ideal flash A/D driver.

The HFA1110 is an enhanced, pin compatible upgrade for the AD9620, AD9630, CLC110, EL2072, BUF600 and BUF601.

For buffer applications requiring a standard op amp pinout, or selectable gain (-1, +1, +2), see the HFA1112 data sheet. For output limiting see the HFA1113 data sheet.

For military grade product please refer to the HFA1110/883 data sheet.

#### **Pinout**



#### Pin Descriptions

NAME	PIN NUMBER	DESCRIPTION
V+	1	Positive Supply
Opt V+	2	Optional Positive Supply
NC	3	No Connection
IN	4	Input
V-	5	Negative Supply
Opt V-	6	Optional Negative Supply
NC	7	No Connection
OUT	8	Output

#### **Features**

Wide -3dB Bandwidth750MHz
• Very Fast Slew Rate
• Fast Settling Time (0.2%)
High Output Current
• Fixed Gain of +1
• Gain Flatness (100MHz) 0.03dB
• Differential Phase
Differential Gain
• 3rd Harmonic Distortion (50MHz)80dBc
3rd Order Intercept (100MHz)

• Pb-Free Plus Anneal Available (RoHS Compliant)

#### **Applications**

- · Video Switching and Routing
- RF/IF Processors
- Driving Flash A/D Converters
- · High-Speed Communications
- Impedance Transformation
- Line Driving
- Radar Systems

#### **Ordering Information**

PART NUMBER	PART MARKING	TEMP. RANGE (°C)	PACKAGE	PKG. DWG.#		
HFA1110IB	1110IB	-40 to 85	8 Ld SOIC	M8.15		
HFA1110IBZ (Note)	1110IBZ -40 to 85 8 Ld SOIC (Pb-free) M8.15					
HFA1110EVAL	High Speed Buffer DIP Evaluation Board					

NOTE: Intersil Pb-free plus anneal products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which are RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

#### HFA1110

#### **Absolute Maximum Ratings**

# Voltage Between V+ and V .12V DC Input Voltage VSUPPLY Output Current 60mA

#### **Operating Conditions**

Temperature Range . . . . . . . . . . . -40°C to 85°C

#### **Thermal Information**

Thermal Resistance (Typical, Note 1)	θ <sub>JA</sub> (°C/W)
SOIC Package	158
Maximum Junction Temperature (Plastic Package)	
Maximum Storage Temperature Range65	5°C to 150°C
Maximum Lead Temperature (Soldering 10s)	300°C
(SOIC - Lead Tips Only)	

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

#### NOTE:

1.  $\theta_{JA}$  is measured with the component mounted on an evaluation PC board in free air.

**Electrical Specifications**  $V_{SUPPLY} = \pm 5V$ ,  $R_L = 100\Omega$ , Unless Otherwise Specified

PARAMETER	TEST CONDITIONS	TEMP (°C)	MIN	TYP	MAX	UNITS
INPUT CHARACTERISTICS	•			•		•
Output Offset Voltage (Note 2)		25	=	8	25	mV
		Full	=	-	35	mV
Output Offset Voltage Drift		Full	-	10	-	μV/°C
PSRR		25	39	45	-	dB
		Full	35	-	-	dB
Input Noise Voltage (Note 2)	100kHz	25	-	14	-	nV/√Hz
Input Noise Current (Note 2)	100kHz	25	-	51	-	pA/√Hz
Input Bias Current (Note 2)		25	-	10	40	μА
		Full	-	-	65	μА
Input Resistance		25	25	50	-	kΩ
Input Capacitance		25	-	2	-	pF
TRANSFER CHARACTERISTICS						
Gain	$V_{OUT} = 2V_{P-P}$	25	0.980	0.990	1.02	V/V
		Full	0.975	-	1.025	V/V
DC Non-Linearity (Note 2)	±2V Full Scale	25	-	0.003	-	%
OUTPUT CHARACTERISTICS					<u> </u>	
Output Voltage (Note 2)		25	3.0	3.3	-	±V
		Full	2.5	3.0	-	±V
Output Current (Note 2)	$R_L = 50\Omega$	25, 85	50	60	-	mA
		-40	35	50	-	mA
POWER SUPPLY CHARACTERIS	TICS					
Supply Voltage Range		Full	4.5	-	5.5	±V
Supply Current (Note 2)		25	=	21	26	mA
		Full	=	-	33	mA
AC CHARACTERISTICS						
-3dB Bandwidth (Note 2)	V <sub>OUT</sub> = 0.2V <sub>P-P</sub>	25	-	750	-	MHz
Slew Rate	$V_{OUT} = 5V_{P-P}$	25	=	1300	-	V/μs
Full Power Bandwidth (Note 2)	$V_{OUT} = 4V_{P-P}$	25	=	150	-	MHz
Gain Flatness (Note 2)	To 100MHz	25	-	±0.03	-	dB
	To 30MHz	25	-	±0.01	-	dB
Linear Phase Deviation (Note 2)	DC to 100MHz	25	=	±0.3	-	0
2nd Harmonic Distortion (Note 2)	50MHz, V <sub>OUT</sub> = 2V <sub>P-P</sub>	25	-	-60	-	dBc
3rd Harmonic Distortion (Note 2)	50MHz, $V_{OUT} = 2V_{P-P}$	25	-	-80	-	dBc
3rd Order Intercept (Note 2)	100MHz	25	=	30	_	dBm

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**Electrical Specifications**  $V_{SUPPLY} = \pm 5V$ ,  $R_L = 100\Omega$ , Unless Otherwise Specified (Continued)

PARAMETER	TEST CONDITIONS	TEMP (°C)	MIN	TYP	- -	UNITS
-1dB Gain Compression	100MHz	25	-	14		dBm
Reverse Gain (S <sub>12</sub> , Note 2)	100MHz, V <sub>OUT</sub> = 1V <sub>P-P</sub>	25	-	-60		dB
TRANSIENT RESPONSE		·				
Rise Time	V <sub>OUT</sub> = 0.5V Step	25	-	0.5	-	ns
Overshoot (Note 2)	V <sub>OUT</sub> = 1.0V Step, Input Signal Rise/Fall = 1ns	25	-	2.5	-	%
0.2% Settling Time (Note 2)	V <sub>OUT</sub> = 1V to 0V	25	-	7	-	ns
0.1% Settling Time (Note 2)	V <sub>OUT</sub> = 1V to 0V	25	-	11	-	ns
Overdrive Recovery Time	verdrive Recovery Time		-	15	-	ns
Differential Gain	3.58MHz, $R_L = 75Ω$	25	-	0.04	-	%
Differential Phase	3.58MHz, $R_L = 75\Omega$	25	-	0.025	-	o

#### NOTE:

2. See Typical Performance Curves for more information.

#### **Application Information**

#### PC Board Layout

The frequency performance of this amplifier depends a great deal on the amount of care taken in designing the PC board. The use of low inductance components such as chip resistors and chip capacitors is strongly recommended, while a solid ground plane is a must!

Attention should be given to decoupling the power supplies. A large value ( $10\mu F$ ) tantalum in parallel with a small value chip ( $0.1\mu F$ ) capacitor works well in most cases.

Terminated microstrip signal lines are recommended at the input and output of the device. Output capacitance, such as that resulting from an improperly terminated transmission line will degrade the frequency response of the amplifier and may cause oscillations. In most cases, the oscillation can be avoided by placing a resistor (Rs) in series with the output. See the "Recommended Rs vs Load Capacitance" graph for specific recommendations.

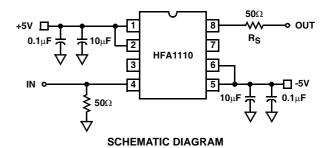
An example of a good high frequency layout is the Evaluation Board shown below.

#### **Evaluation Board**

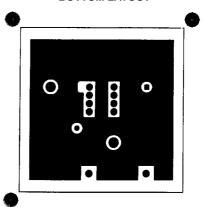
An evaluation board is available for the HFA1110 (part number HFA1110EVAL). Please contact your local sales office for information.

The layout and schematic of the board are shown here:

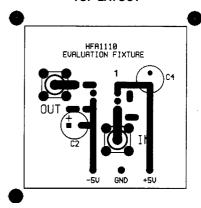
NOTE: The SOIC version may be evaluated in the DIP board by using a SOIC-to-DIP adapter such as Aries Electronics Part Number 08-350000-10.



**BOTTOM LAYOUT** 



TOP LAYOUT



### $\textbf{Typical Performance Curves} \quad \text{$V_{SUPPLY}$ = $\pm 5$V, $T_A$ = $25^{\circ}$C, $R_L$ = $100\Omega$, Unless Otherwise Specified and the support of the support of$

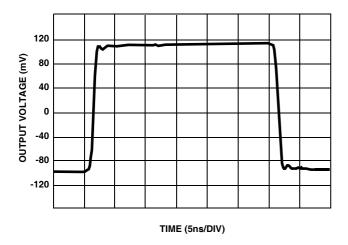


FIGURE 1. SMALL SIGNAL PULSE RESPONSE

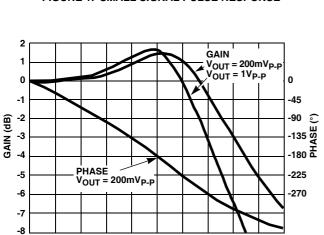


FIGURE 3. FREQUENCY RESPONSE

FREQUENCY (Hz)

600M

800M

1G

400M

0

200M

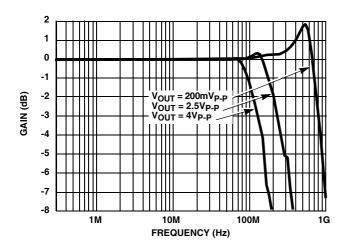


FIGURE 5. FREQUENCY RESPONSE FOR VARIOUS OUTPUT VOLTAGES

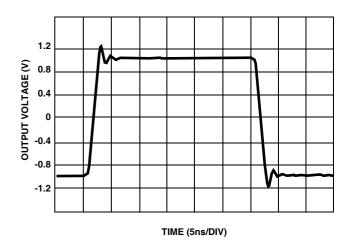


FIGURE 2. LARGE SIGNAL PULSE RESPONSE

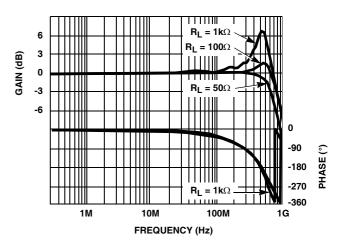


FIGURE 4. FREQUENCY RESPONSE FOR VARIOUS LOAD RESISTORS

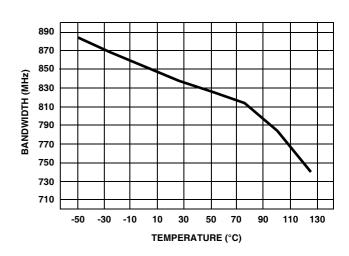


FIGURE 6. -3dB BANDWIDTH vs TEMPERATURE

 $\textbf{Typical Performance Curves} \quad \text{$V_{SUPPLY}$ = $\pm 5$V, $T_A$ = $25^{\circ}$C, $R_L$ = $100\Omega$, Unless Otherwise Specified (Continued) and the support of the$ 

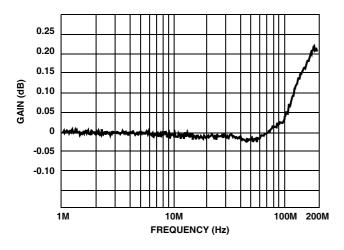


FIGURE 7. GAIN FLATNESS

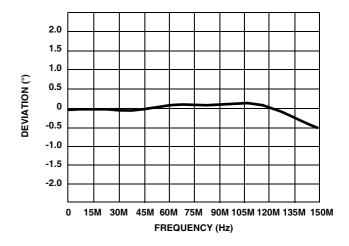


FIGURE 8. DEVIATION FROM LINEAR PHASE

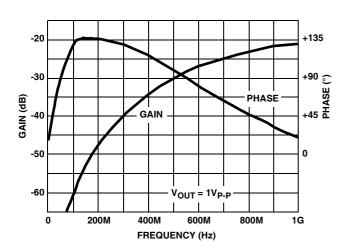


FIGURE 9. REVERSE GAIN AND PHASE (S<sub>12</sub>)

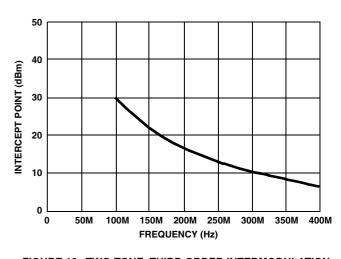


FIGURE 10. TWO-TONE, THIRD ORDER INTERMODULATION INTERCEPT

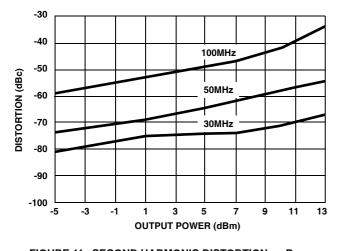


FIGURE 11. SECOND HARMONIC DISTORTION vs  $P_{OUT}$ 

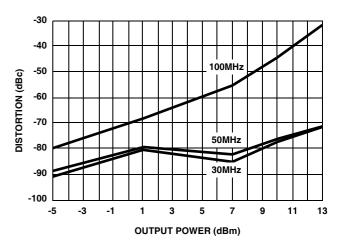


FIGURE 12. THIRD HARMONIC DISTORTION vs POUT

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### $\textbf{Typical Performance Curves} \quad \text{$V_{SUPPLY} = \pm 5V$, $T_A = 25^{\circ}C$, $R_L = 100\Omega$, Unless Otherwise Specified (Continued) and the property of the proper$

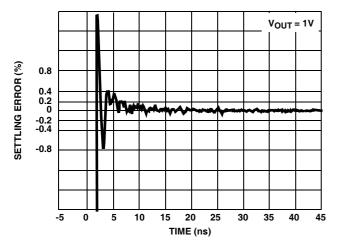


FIGURE 13. SETTLING RESPONSE

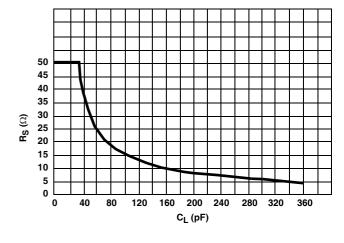


FIGURE 14. RECOMMENDED SERIES OUTPUT RESISTOR vs  $\mathsf{C}_{\mathsf{LOAD}}$ 

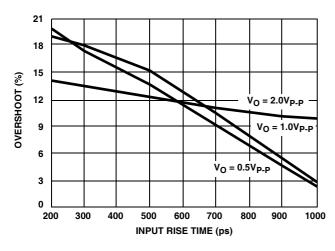


FIGURE 15. OVERSHOOT vs INPUT RISETIME

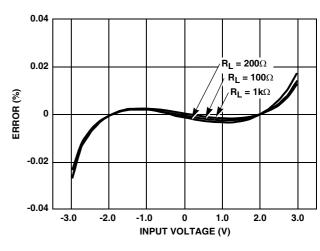


FIGURE 16. INTEGRAL LINEARITY ERROR

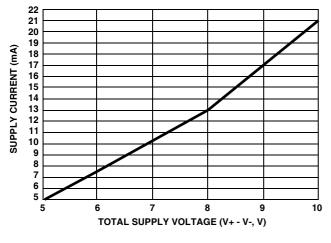


FIGURE 17. SUPPLY CURRENT vs SUPPLY VOLTAGE

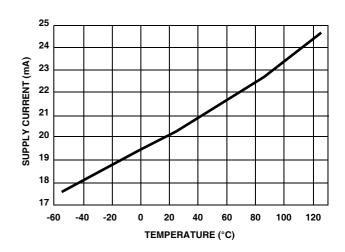


FIGURE 18. SUPPLY CURRENT vs TEMPERATURE

### $\textbf{\textit{Typical Performance Curves}} \quad \text{V}_{SUPPLY} = \pm 5 \text{V}, \text{ T}_{A} = 25 ^{\circ}\text{C}, \text{ R}_{L} = 100 \Omega, \text{Unless Otherwise Specified} \text{ (Continued)}$

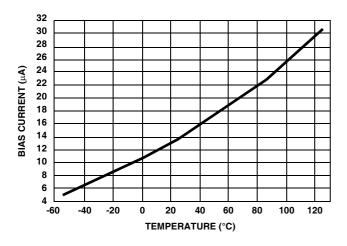


FIGURE 19. BIAS CURRENT vs TEMPERATURE

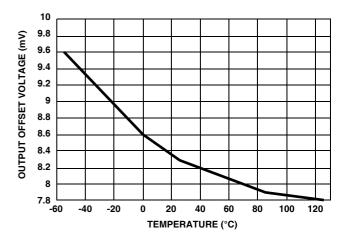


FIGURE 20. OFFSET VOLTAGE vs TEMPERATURE

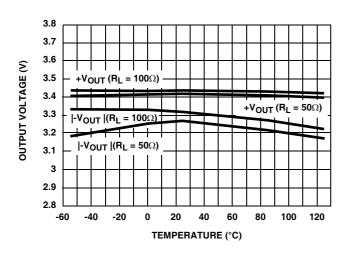


FIGURE 21. OUTPUT VOLTAGE vs TEMPERATURE

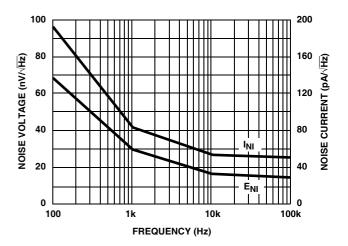


FIGURE 22. INPUT NOISE vs FREQUENCY

#### Die Characteristics

#### **DIE DIMENSIONS:**

63 mils x 44 mils x 19 mils 1600μm x 1130μm x 483μm

#### **METALLIZATION:**

Type: Metal 1: AlCu(2%)/TiW Thickness: Metal 1: 8kÅ ±0.4kÅ Type: Metal 2: AlCu(2%)

Thickness: Metal 2: 16kÅ ±0.8kÅ

### **PASSIVATION:**

Type: Nitride

Thickness: 4kÅ ±0.5kÅ

#### TRANSISTOR COUNT:

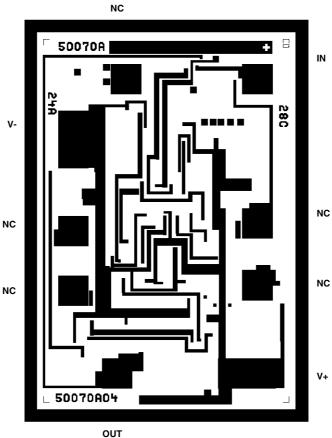
52

#### SUBSTRATE POTENTIAL (POWERED UP):

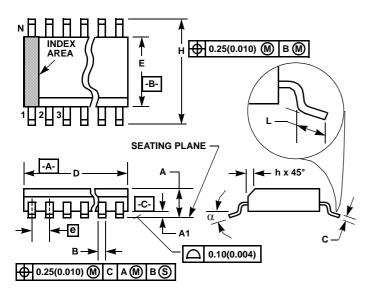
Floating (Recommend Connection to V-)

### Metallization Mask Layout

HFA1110



#### Small Outline Plastic Packages (SOIC)



#### NOTES:

- Symbols are defined in the "MO Series Symbol List" in Section 2.2 of Publication Number 95.
- 2. Dimensioning and tolerancing per ANSI Y14.5M-1982.
- Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion and gate burrs shall not exceed 0.15mm (0.006 inch) per side.
- Dimension "E" does not include interlead flash or protrusions. Interlead flash and protrusions shall not exceed 0.25mm (0.010 inch) per side.
- 5. The chamfer on the body is optional. If it is not present, a visual index feature must be located within the crosshatched area.
- 6. "L" is the length of terminal for soldering to a substrate.
- 7. "N" is the number of terminal positions.
- 8. Terminal numbers are shown for reference only.
- 9. The lead width "B", as measured 0.36mm (0.014 inch) or greater above the seating plane, shall not exceed a maximum value of 0.61mm (0.024 inch).
- Controlling dimension: MILLIMETER. Converted inch dimensions are not necessarily exact.

M8.15 (JEDEC MS-012-AA ISSUE C) 8 LEAD NARROW BODY SMALL OUTLINE PLASTIC PACKAGE

	INCHES		MILLIN		
SYMBOL	MIN	MAX	MIN	MAX	NOTES
Α	0.0532	0.0688	1.35	1.75	-
A1	0.0040	0.0098	0.10	0.25	-
В	0.013	0.020	0.33	0.51	9
С	0.0075	0.0098	0.19	0.25	-
D	0.1890	0.1968	4.80	5.00	3
Е	0.1497	0.1574	3.80	4.00	4
е	0.050 BSC		1.27 BSC		-
Н	0.2284	0.2440	5.80	6.20	-
h	0.0099	0.0196	0.25	0.50	5
L	0.016	0.050	0.40	1.27	6
N	8		8		7
α	0°	8°	0°	8°	-

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